

Dual N-Channel MOSFET

General Description

The WSD4078DN56 is the highest performance trench Dual N-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WSD4078DN56 meet the RoHS and Green Product requirement, 100% E_{AS} guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% E_{AS} Guaranteed
- Green Device Available

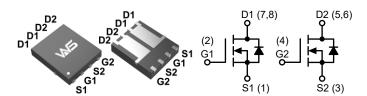
Product Summery

BV _{DSS}	R _{DS(ON)}	I _D
40V	7.0mΩ	40A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

DFN5X6-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V	40	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V	28	A
I _{DM}	Pulse Drain Current ⁷	180	
E _{AS}	Single Pulse Avalanche Energy ³	10	mJ
I _{AS}	Avalanche Current	14	Α
P _D @T _C =25°C	Total Power Dissipation	31	W
T _{STG}	T _{STG} Storage Temperature Range		°C
T _J	T _J Operating Junction Temperature Range		

Thermal Data

Symbol	Parameter	Тур.	Max.	Units
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		55	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		4.1	C/VV

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Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250μA	40			٧
$\Delta BV_{DSS}/\Delta T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA		0.043		V/°C
В	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =20A		7.0	9.5	- mΩ
R _{DS(ON)}		V _{GS} =4.5V , I _D =15A		11	15	
V _{GS(th)}	Gate Threshold Voltage	\\ _\\	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_{D}=250\mu A$		-6.94		mV/°C
	Duein Course Legles of Course	V _{DS} =32V , V _{GS} =0V ,T _J =25°C			2.0	
I _{DSS}	Drain-Source Leakage Current	V _{DS} =32V , V _{GS} =0V , T _J =55°C			10	μA 0
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =20A		13		S
R_{g}	Gate Resistance	V _{DS} =0V , V _{GS} =0V , <i>f</i> =1.0MHz		0.8		Ω
Q_g	Total Gate Charge (10V)	V _{DS} =20V , V _{GS} =10V , I _D =20A		9.4		
Q_{gs}	Gate-Source Charge			1.9		nC
Q_{gd}	Gate-Drain Charge			6.0		
$T_{d(on)}$	Turn-On Delay Time			12		
T _r	Rise Time	V_{DD} =20V , V_{GEN} =10V , R_{G} =1 Ω I_{D} =1A , R_{L} =15 Ω		10		
T _{d(off)}	Turn-Off Delay Time			25		ns
T _f	Fall Time			11		
C _{iss}	Input Capacitance	V _{DS} =20V , V _{GS} =0V , <i>f</i> =1.0MHz		700		
C _{oss}	Output Capacitance			132		pF
C _{rss}	Reverse Transfer Capacitance			108		

Diode Characteristics

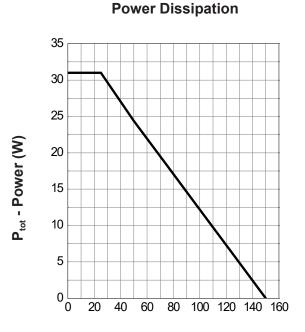
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
I _S	Continuous Source Current 1,6	V _G =V _D =0V , Force Current			25	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10sec.
- 2. The data tested by pulsed, pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$.
- 3. The E $_{\rm AS}$ data shows Max. rating . The test condition is $\rm\,V_{DD}$ =25V, $\rm\,V_{GS}$ =10V, L=0.1mH, I $_{\rm AS}$ =14A
- 4. The power dissipation is limited by 150°C junction temperature.
- 5. The Min. value is 100% $\,{\rm E}_{\rm AS}\,$ tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.
- 7. Package limitation current.

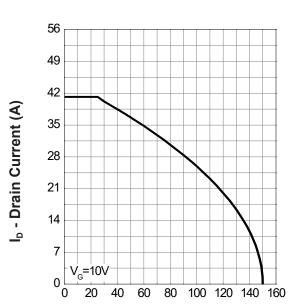


Typical Characteristics



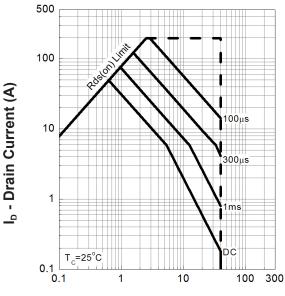
T_c - Case Temperature (°C)

Drain Current



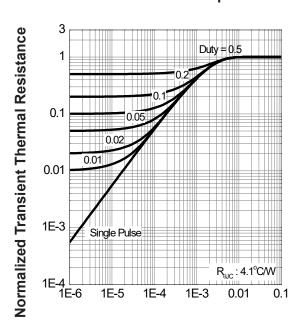
T_c - Case Temperature (°C)

Safe Operation Area



V_{DS} - Drain - Source Voltage (V)

Thermal Transient Impedance

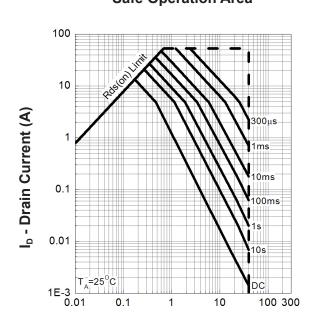


Square Wave Pulse Duration (sec)



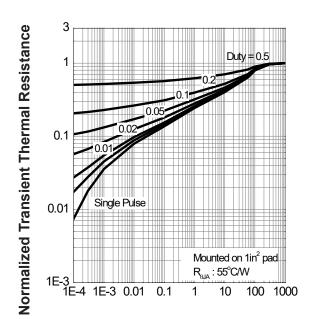
Typical Characteristics (Cont.)

Safe Operation Area



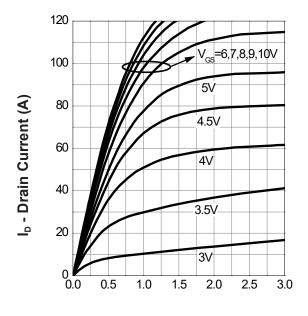
V_{DS} - Drain - Source Voltage (V)

Thermal Transient Impedance



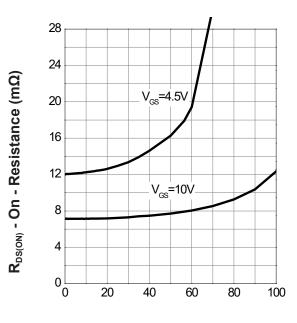
Square Wave Pulse Duration (sec)

Output Characteristics



V_{DS} - Drain - Source Voltage (V)

Drain-Source On Resistance

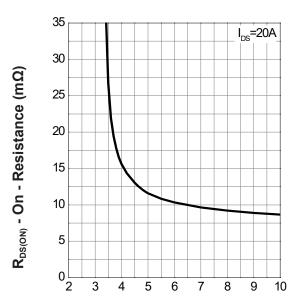


I_D - Drain Current (A)



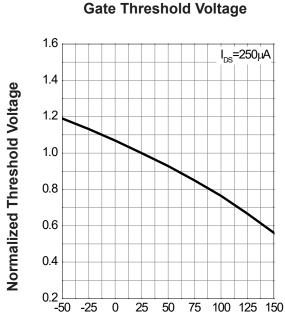
Typical Characteristics (Cont.)

Gate-Source On Resistance



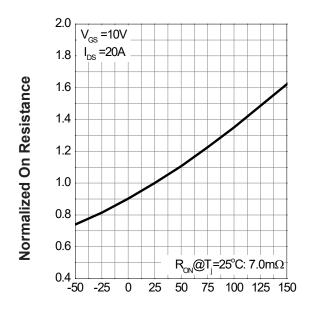
V_{GS} - Gate - Source Voltage (V)

Gate-Source Off Resistance



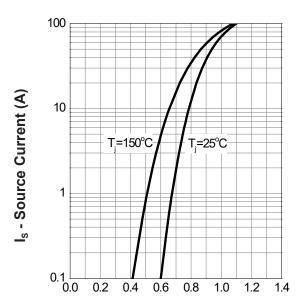
T_j - Junction Temperature (°C)

Drain-Source On Resistance



T_j - Junction Temperature (°C)

Source-Drain Diode Forward



V_{SD} - Source - Drain Voltage (V)



Typical Characteristics (Cont.)

Capacitance Frequency=1MHz Ciss C - Capacitance (pF) Coss

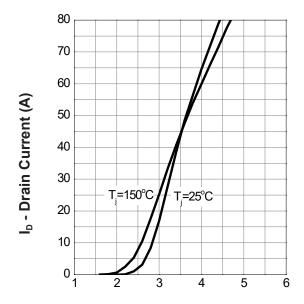
V_{DS} - Drain-Source Voltage (V)

V_{DS}=20V I_{DS}=20A V_{GS} - Gate-source Voltage (V)

Gate Charge

Q_G - Gate Charge (nC)

Transfer Characteristics

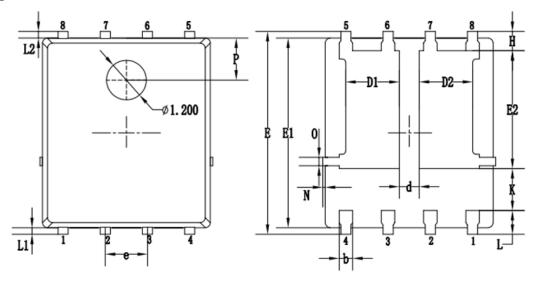


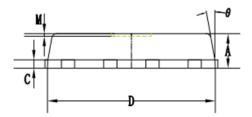
V_{GS} - Gate-Source Voltage (V)



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Packaging information





0)////		MILLIMETERS				
SYMBOLS	MIN.	NOM.	MAX.			
Α	0.90	1.05	1.20			
b	0.35	0.40	0.50			
С	0.20	0.25	0.35			
D	4.90	5.05	5.20			
D1/D2	1.51	1.61	1.71			
d	0.50	0.60	0.70			
E	6.00	6.15	6.30			
E1	5.60	5.75	5.90			
E2	3.47	3.57	3.67			
е		1.27 BSC.				
Н	0.48	0.58	0.68			
K	1.17	1.27	1.37			
L	0.64	0.74	0.84			
L1/L2		0.20 REF.				
θ	8°	10°	12°			
М		0.08 REF.				
N	0	-	0.15			
0		0.25 REF.				
Р		1.28 REF.				



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